

SAMTM Data Sheet SAM-2800-34-10ps-x, λ = 2800 nm

Laser wavelength $\lambda = 2800 \text{ nm}$

High reflection band $\lambda = 2600 ... 3200 \text{ nm}$

Absorbance $A_0 = 34 \%$ Modulation depth $\Delta R = 20 \%$ Non-saturable loss $A_{ns} = 14 \%$

Saturation fluence $\Phi_{\text{sat}} = 70 \,\mu\text{J/cm}^2$

Relaxation time constant $\tau \sim 10 \text{ ps}$

Damage threshold $\Phi = 1 \text{ mJ/cm}^2$

Chip area 4.0 mm x 4.0 mm; other dimensions on request

Chip thickness 625 µm

Reverse design The laser beam is supplied through the AR coated GaAs substrate

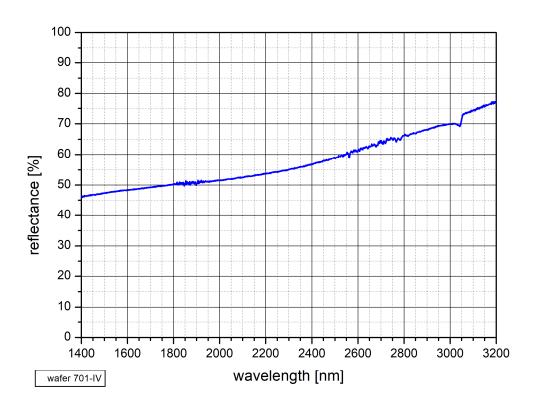
Please see figure below on page 2

Mounting option **x** denotes the type of mounting as follows:

x = 0 unmounted

 \mathbf{x} = 12.7 gglued on a gold plated Cu-cylinder with 12.7 mm \varnothing \mathbf{x} = 25.4 gglued on a gold plated Cu-cylinder with 25.4 mm \varnothing

Low intensity spectral reflectance



Data Sheet



Reverse design of the SAM-2800-20-10ps-x

